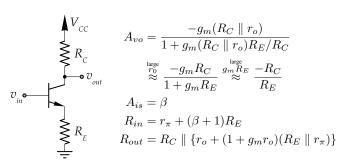
Single Transistor Amplifiers

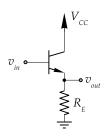
Common Emitter Amplifier

Reasonable Gain. Adjustable input impedance. Relatively high output impedance. Good inverting voltage amp (If the load is known!)



Common Collector Amplifier

Nice voltage buffer: High R_{in} and low R_{out} . "Copies the input voltage to an unknown load".



$$V_{cc}$$

$$A_{vo} = \frac{R_E \parallel r_o}{r_e + R_E \parallel r_o} \approx 1$$

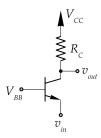
$$A_{is} = \beta + 1$$

$$R_{in} = r_\pi + (\beta + 1)(R_E \parallel r_o)$$

$$R_{out} = r_e \parallel R_E \parallel r_o \approx r_e$$

Common Base Amplifier

Nice current buffer: Low R_{in} and high R_{out} . "Copies the input current to an unknown load". Also used as a noninverting voltage amp-IF you know the load, and need a low input resistance.



$$A_{vo} = g_m(r_o \parallel R_C)$$

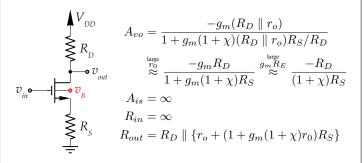
$$A_{is} = \alpha \approx 1$$

$$R_{in} = r_e + \frac{R_C}{g_m r_o} \stackrel{r_0 \gg R_C}{\approx} r_e$$

$$R_{out} = R_C \parallel r_o$$

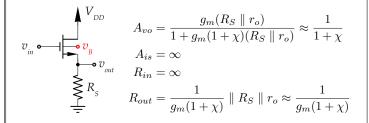
Common Source Amplifier

Reasonable Gain. Adjustable input impedance. Relatively high output impedance. Good inverting voltage amp (If the load is known!)



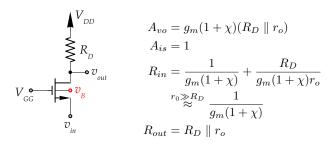
Common Drain Amplifier

Nice voltage buffer: Infinite R_{in} and low R_{out} . "Copies the input voltage to an unknown load".



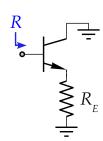
Common Gate Amplifier

Nice current buffer: Low R_{in} and high R_{out} . "Copies the input current to an unknown load". Also used as a noninverting voltage ampif you know the load, and need a low input resistance.



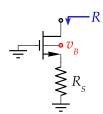
(All expressions assume v_B is constant. If $v_{BS} = 0$, set $\chi = 0$.)

Small-Signal Impedance Measured at Transistor Terminals



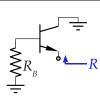
Emitter Impedances seen through the base of a BJT are *increased* by a factor of $\beta + 1$.

$$R \approx r_{\pi} + (\beta + 1)R_E$$



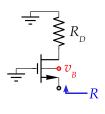
Impedances seen through the drain of a MOS-FET are *increased* by the intrinsic gain of the transistor. Use $g'_m = g_m + g_{mb} = (1 + \chi)g_m$:

$$R = r_0 + (1 + g'_m r_0) R_S$$



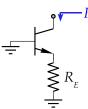
Base Impedances seen through the emitter of a BJT are *decreased* by a factor of $\beta + 1$.

$$R \approx \frac{r_{\pi} + R_B}{\beta + 1} = r_e + \frac{R_B}{\beta + 1}$$



Impedances seen through the source of a MOS-FET are *reduced* by the intrinsic gain of the transistor. Use $g_m' = g_m + g_{mb} = (1 + \chi)g_m$:

$$\begin{split} R &= \frac{1}{g_m'} \parallel r_0 + \frac{R_D}{1 + g_m' r_0} \\ &\approx \frac{1}{g_m'} + \frac{R_D}{g_m' r_0} \stackrel{r_0 \gg R_D}{\approx} \frac{1}{g_m'} \end{split}$$

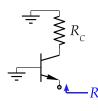


Impedances seen through the collector of a BJT are *increased* by the intrinsic gain of the transistor. Loads attached to the emitter are in parallel with r_{π} .

$$R = r_0 + (1 + g_m r_0)(R_E \parallel r_\pi)$$

With a base resistor, R_B is added to r_{π} , and g_m is scaled by $\left(\frac{r_{\pi}}{r_{\pi}+R_B}\right)$:

$$R = r_0 + \left(1 + \left(\frac{r_{\pi}}{r_{\pi} + R_B}\right) g_m r_0\right) (R_E \parallel (r_{\pi} + R_B))$$



Collector impedances seen through the emitter of a BJT are are *decreased* by the intrinsic gain of the transistor.

$$\begin{split} R &= r_{\pi} \parallel \left(\frac{1}{g_m} \parallel r_0 + \frac{R_C}{1 + g_m r_0}\right) \\ &\approx r_{\pi} \parallel \left(\frac{1}{g_m} + \frac{R_C}{g_m r_0}\right) \\ &\stackrel{r_0 \gg R_C}{\approx} r_{\pi} \parallel \frac{1}{g_m} = r_e \end{split}$$

With a base resistor, R_B is added to r_{π} , and g_m is scaled by $\left(\frac{r_{\pi}}{r_{\pi}+R_B}\right)$:

$$R = (r_{\pi} + R_B) \parallel \left(\frac{1}{\left(\frac{r_{\pi}}{r_{\pi} + R_B}\right) g_m} \parallel r_0 + \frac{R_C}{1 + \left(\frac{r_{\pi}}{r_{\pi} + R_B}\right) g_m r_0} \right)$$

All expressions assume v_B is constant.

$$g'_{m} = g_{m} + g_{mb} = g_{m}(1 + \chi)$$

If $v_{BS} = 0$, set $\chi = 0$.